

DATA SHEET

PDTA143T series

PNP resistor-equipped transistors;
R1 = 4.7 k Ω , R2 = open

Product specification
Supersedes data of 2002 Jan 15

2003 Apr 10

PNP resistor-equipped transistors; R1 = 4.7 k Ω , R2 = open

PDTA143T series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CEO}	collector-emitter voltage	–	–50	V
I _O	output current (DC)	–	–100	mA
R1	bias resistor	4.7	–	k Ω
R2	open	–	–	–

DESCRIPTION

PNP resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	NPN COMPLEMENT
	PHILIPS	EIAJ		
PDTA143TEF	SOT490	SC-89	10	PDTC143TEF
PDTA143TK	SOT346	SC-59	45	PDTC143TK
PDTA143TM	SOT883	SC-101	E6	PDTC143TM
PDTA143TS	SOT54 (TO-92)	SC-43	TA143T	PDTC143TS
PDTA143TT	SOT23	–	*42 ⁽¹⁾	PDTC143TT
PDTA143TU	SOT323	SC-70	*45 ⁽¹⁾	PDTC143TU

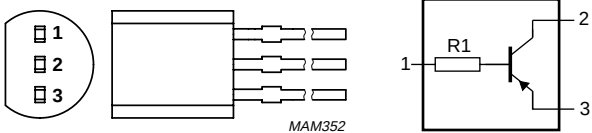
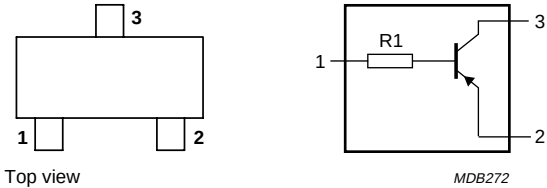
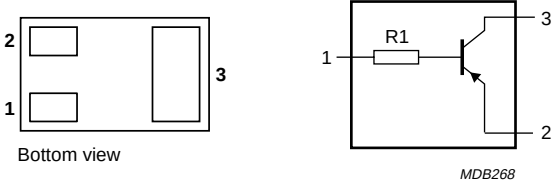
Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

PNP resistor-equipped transistors;
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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTA143TS	 MAM352	1 2 3	base collector emitter
PDTA143TEF PDTA143TK PDTA143TT PDTA143TU	 Top view MDB272	1 2 3	base emitter collector
PDTA143TM	 Bottom view MDB268	1 2 3	base emitter collector

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	–50	V
V _{CEO}	collector-emitter voltage	open base	–	–50	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _O	output current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT490	note 1	500	K/W
	SOT883	notes 2 and 3	500	K/W

Notes

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2. Reflow soldering is the only recommended soldering method.
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CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = -50 V; I _E = 0	–	–	-100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = -30 V; I _B = 0	–	–	-1	μ A
		V _{CE} = -30 V; I _B = 0; T _j = 150 °C	–	–	-50	μ A
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0	–	–	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -1 mA	200	–	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = -5 mA; I _B = -0.25 mA	–	–	-100	mV
R1	input resistor		3.3	4.7	6.1	k Ω
C _c	collector capacitance	I _E = I _e = 0; V _{CB} = -10 V; f = 1 MHz	–	–	3	pF

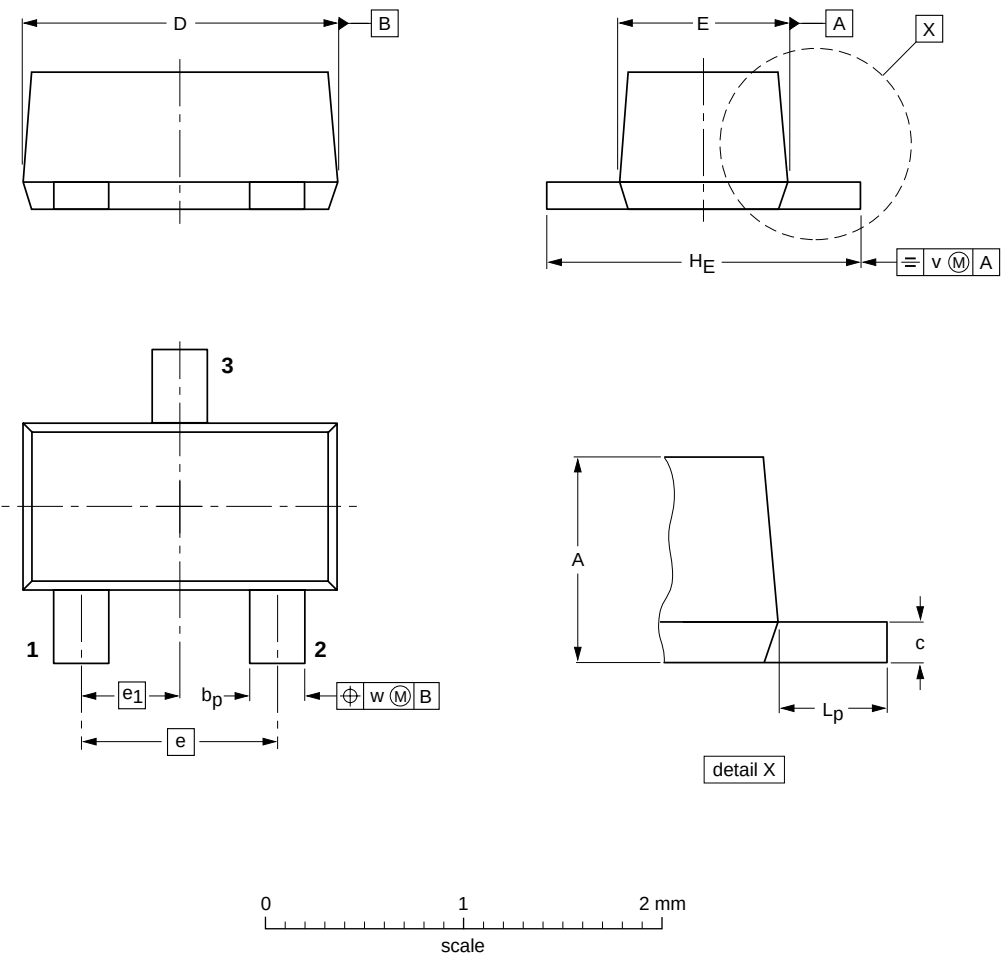
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PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT490



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _p	c	D	E	e	e ₁	H _E	L _p	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

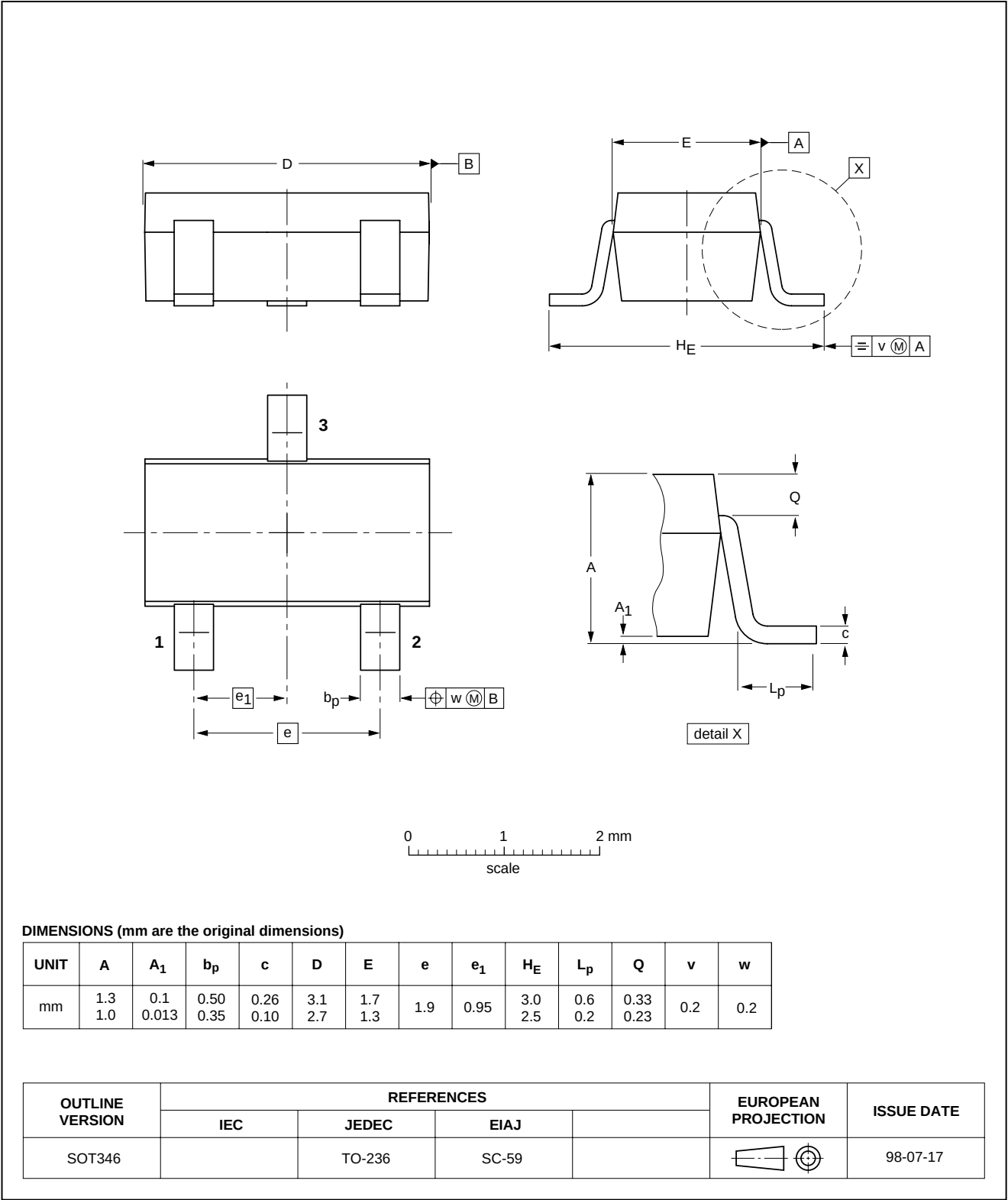
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT490			SC-89			98-10-23

PNP resistor-equipped transistors;
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Plastic surface mounted package; 3 leads

SOT346

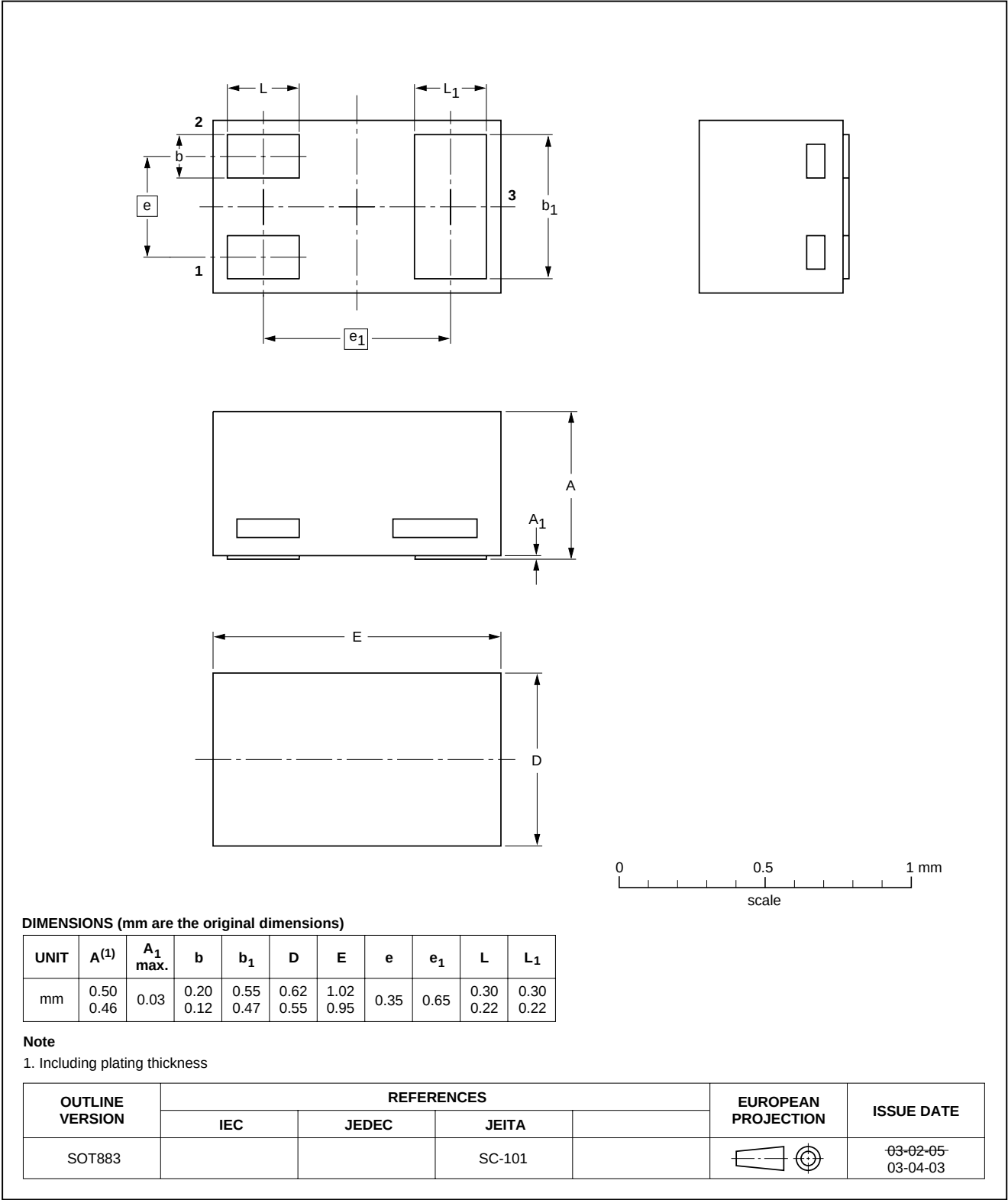


PNP resistor-equipped transistors;
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Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

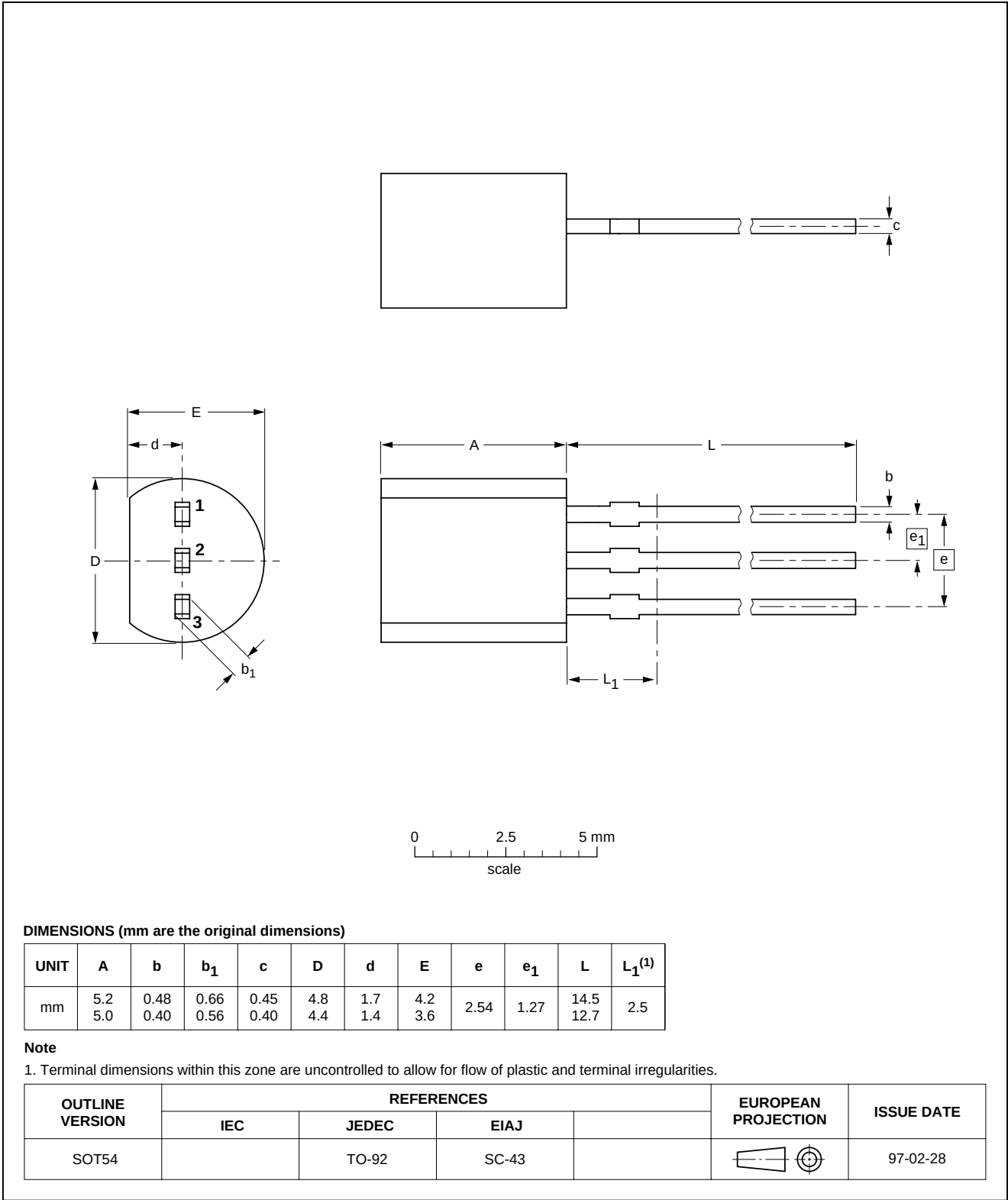


PNP resistor-equipped transistors;
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Plastic single-ended leaded (through hole) package; 3 leads

SOT54

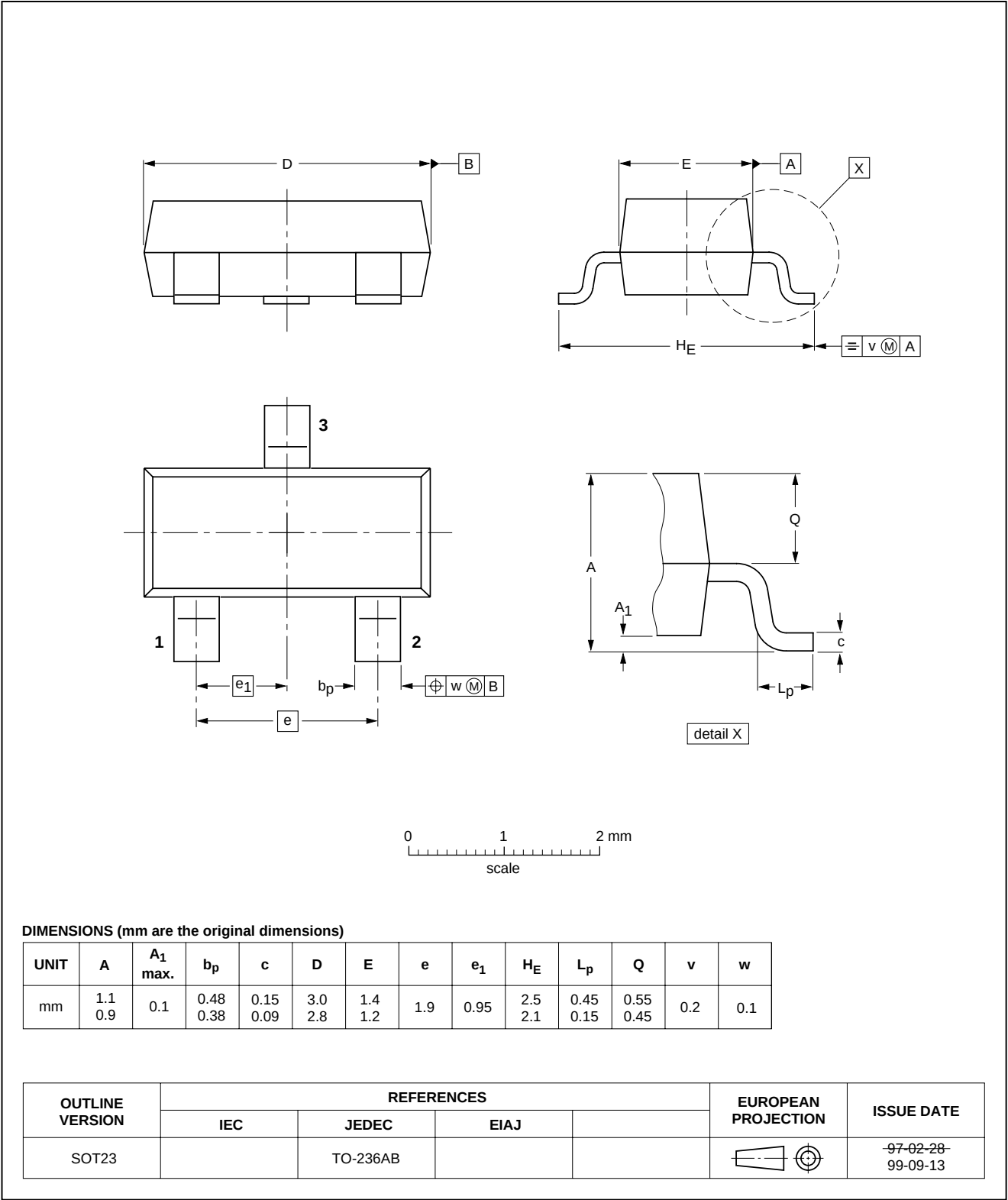


PNP resistor-equipped transistors;
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Plastic surface mounted package; 3 leads

SOT23

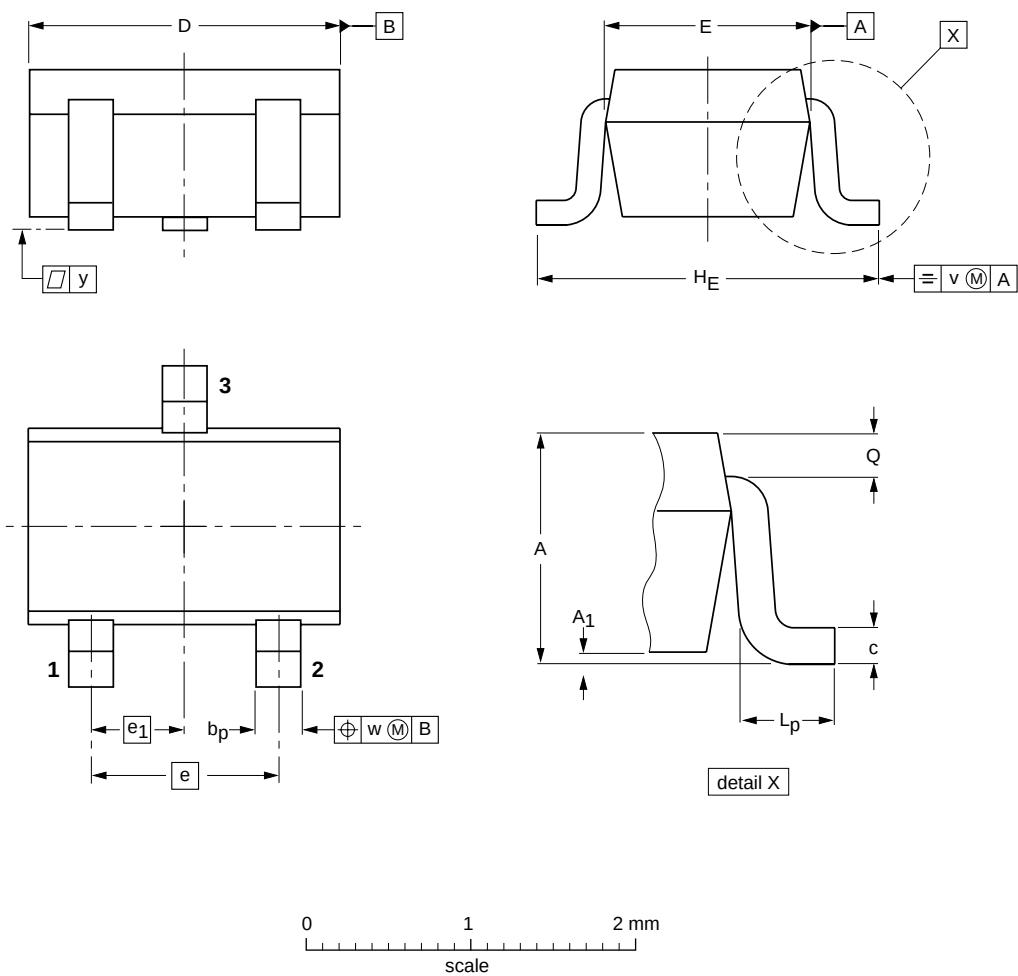


PNP resistor-equipped transistors;
R1 = 4.7 kΩ, R2 = open

PDTA143T series

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A1 max	bp	c	D	E	e	e1	HE	Lp	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

PNP resistor-equipped transistors;
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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Notes

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2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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NOTES

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